

V_{DSS}	200V
$R_{DS(on)}$ (Max.)	770m Ω
I_D	8.0A
P_D	40W

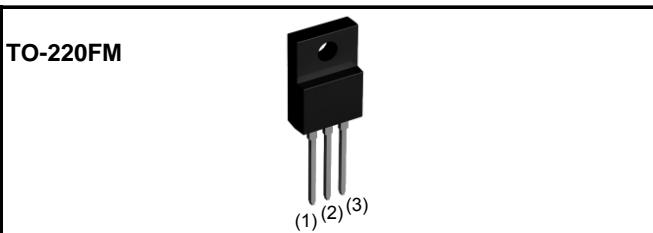
●Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Drive circuits can be simple.
- 4) Parallel use is easy.
- 5) Pb-free lead plating ; RoHS compliant
- 6) 100% Avalanche tested

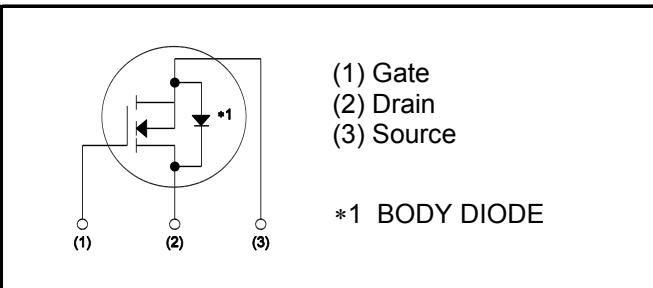
●Application

Switching Power Supply
 Automotive Motor Drive
 Automotive Solenoid Drive

●Outline



●Inner circuit



●Packaging specifications

Type	Packaging	Bulk
	Reel size (mm)	-
	Tape width (mm)	-
	Basic ordering unit (pcs)	500
	Taping code	-
	Marking	RCX081N20

●Absolute maximum ratings($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Drain - Source voltage	V_{DSS}	200	V
Continuous drain current	I_D * ¹	± 8.0	A
	I_D * ¹	± 4.3	A
Pulsed drain current	$I_{D,pulse}$ * ²	± 32	A
Gate - Source voltage	V_{GSS}	± 30	V
Avalanche energy, single pulse	E_{AS} * ³	5.17	mJ
Avalanche current	I_{AR} * ³	4.0	A
Power dissipation	P_D	40	W
	P_D	2.23	W
Junction temperature	T_j	150	°C
Range of storage temperature	T_{stg}	-55 to +150	°C

● Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - case	R _{thJC}	-	-	3.125	°C/W
Thermal resistance, junction - ambient	R _{thJA}	-	-	56	°C/W
Soldering temperature, wavesoldering for 10s	T _{sold}	-	-	265	°C

● Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 1mA	200	-	-	V
Zero gate voltage drain current	I _{DSS}	V _{DS} = 200V, V _{GS} = 0V T _j = 25°C	-	-	10	μA
		V _{DS} = 200V, V _{GS} = 0V T _j = 125°C	-	-	100	
Gate - Source leakage current	I _{GSS}	V _{GS} = ±30V, V _{DS} = 0V	-	-	±100	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} = 10V, I _D = 1mA	3.25	-	5.25	V
Static drain - source on - state resistance	R _{DS(on)} ^{*4}	V _{GS} = 10V, I _D = 4.0A	-	550	770	mΩ
		V _{GS} = 10V, I _D = 4.0A T _j = 125°C	-	1090	1500	
Forward transfer admittance	g _{fs}	V _{DS} = 10V, I _D = 4.0A	1.0	2.0	-	S

● Electrical characteristics($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	C_{iss}	$V_{GS} = 0\text{V}$ $V_{DS} = 25\text{V}$ $f = 1\text{MHz}$	-	330	-	pF
Output capacitance	C_{oss}		-	33	-	
Reverse transfer capacitance	C_{rss}		-	15	-	
Turn - on delay time	$t_{d(on)}^{*4}$	$V_{DD} \approx 100\text{V}, V_{GS} = 10\text{V}$ $I_D = 4.0\text{A}$ $R_L = 25\Omega$ $R_G = 10\Omega$	-	13	-	ns
Rise time	t_r^{*4}		-	20	-	
Turn - off delay time	$t_{d(off)}^{*4}$		-	18	-	
Fall time	t_f^{*4}		-	8	-	

● Gate Charge characteristics($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	Q_g^{*4}	$V_{DD} \approx 100\text{V}$ $I_D = 8.0\text{A}$ $V_{GS} = 10\text{V}$	-	8.5	-	nC
Gate - Source charge	Q_{gs}^{*4}		-	3.4	-	
Gate - Drain charge	Q_{gd}^{*4}		-	3.4	-	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} \approx 100\text{V}, I_D = 4.0\text{A}$	-	7.9	-	V

● Body diode electrical characteristics (Source-Drain)($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Continuous source current	I_S^{*1}	$T_c = 25^\circ\text{C}$	-	-	8.0	A
Pulsed source current	I_{SM}^{*2}		-	-	32	A
Forward voltage	V_{SD}^{*4}	$V_{GS} = 0\text{V}, I_S = 8.0\text{A}$	-	-	1.5	V
Reverse recovery time	t_{rr}^{*4}	$I_S = 4.0\text{A}$ $di/dt = 100\text{A}/\mu\text{s}$	-	75	-	ns
Reverse recovery charge	Q_{rr}^{*4}		-	210	-	nC

*1 Limited only by maximum temperature allowed.

*2 $P_w \leq 10\mu\text{s}$, Duty cycle $\leq 1\%$ *3 $L \approx 500\mu\text{H}$, $V_{DD} = 50\text{V}$, $R_g = 25\Omega$, starting $T_j = 25^\circ\text{C}$

*4 Pulsed

● Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

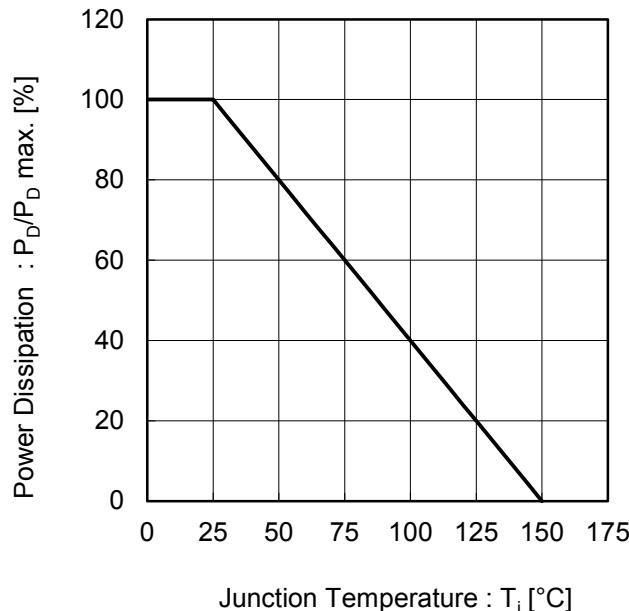


Fig.2 Maximum Safe Operating Area

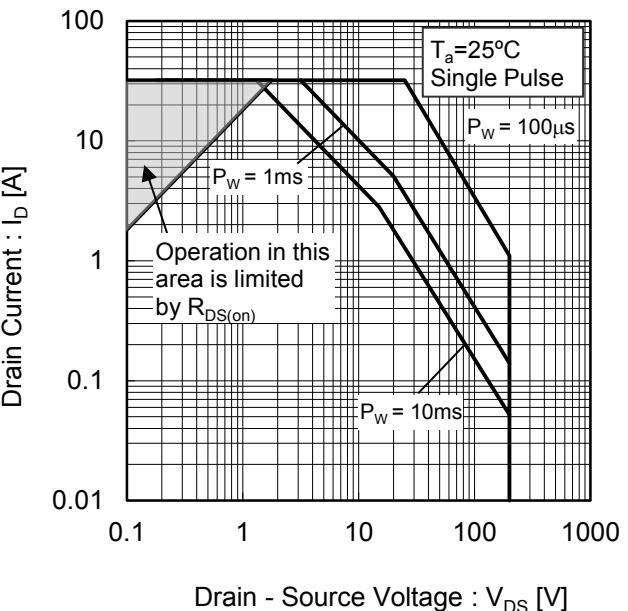
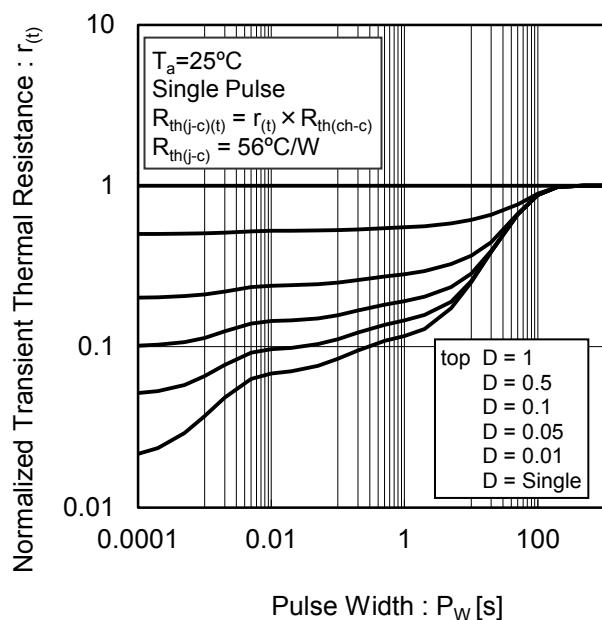


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width



● Electrical characteristic curves

Fig.4 Avalanche Current vs Inductive Load

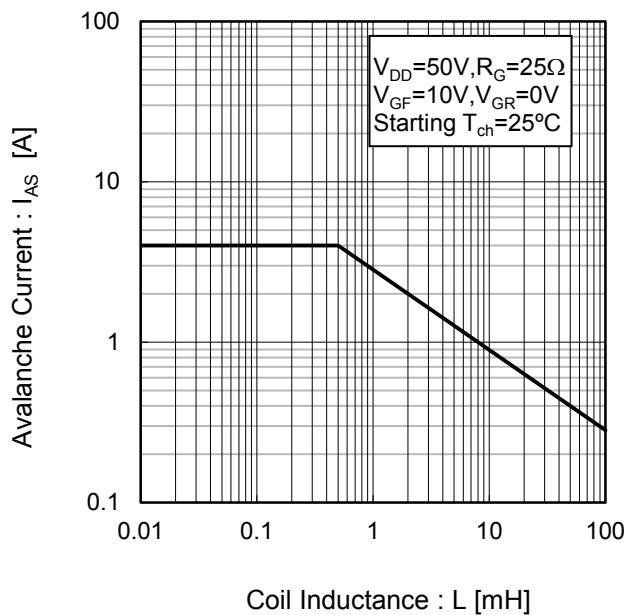


Fig.5 Avalanche Energy Derating Curve vs Junction Temperature

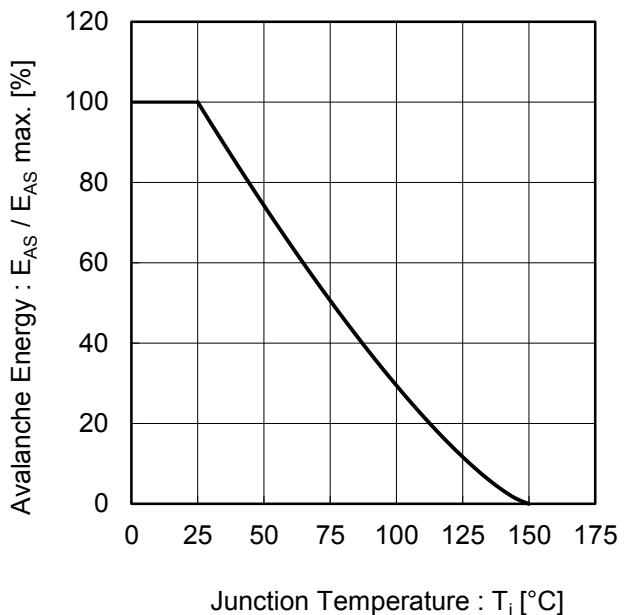


Fig.6 Typical Output Characteristics(I)

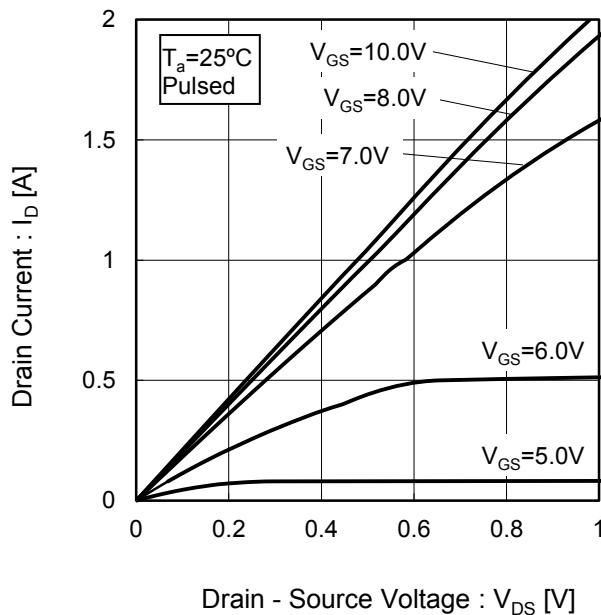
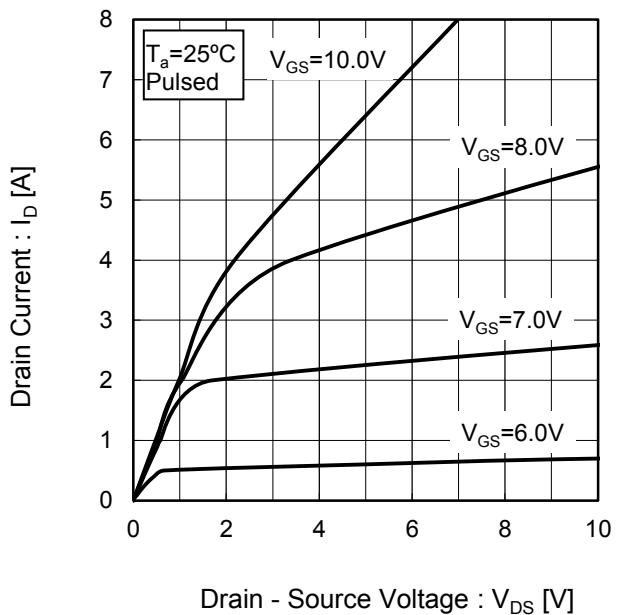


Fig.7 Typical Output Characteristics(II)



● Electrical characteristic curves

Fig.8 Breakdown Voltage
vs. Junction Temperature

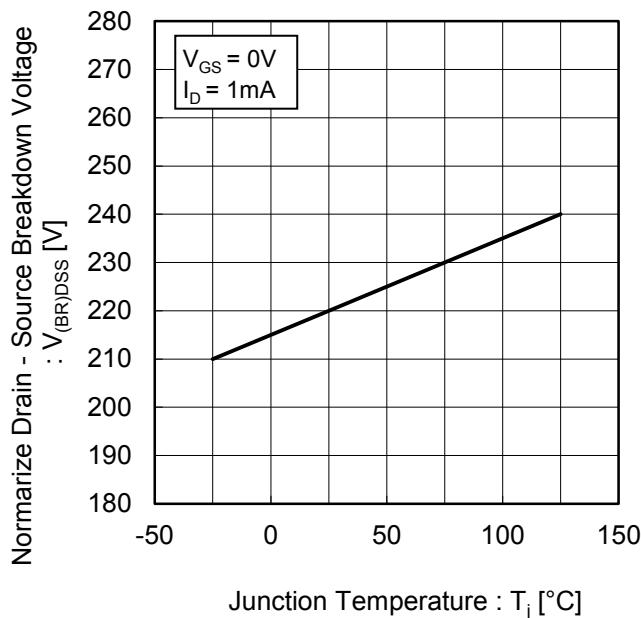


Fig.9 Typical Transfer Characteristics

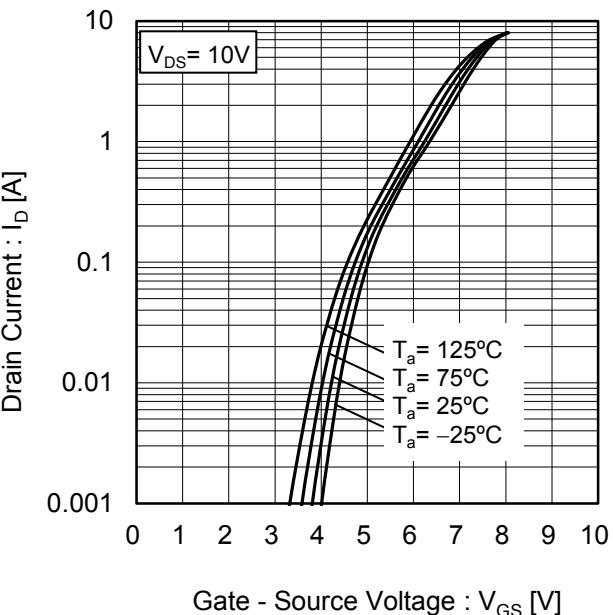


Fig.10 Gate Threshold Voltage
vs. Junction Temperature

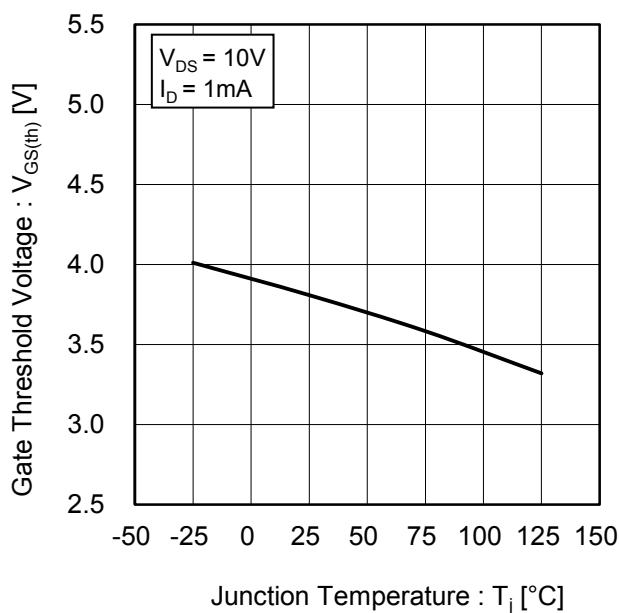
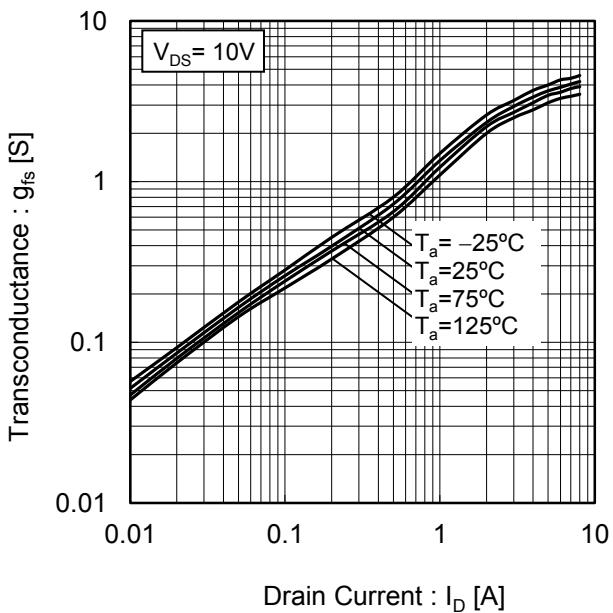


Fig.11 Transconductance vs. Drain Current



● Electrical characteristic curves

Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

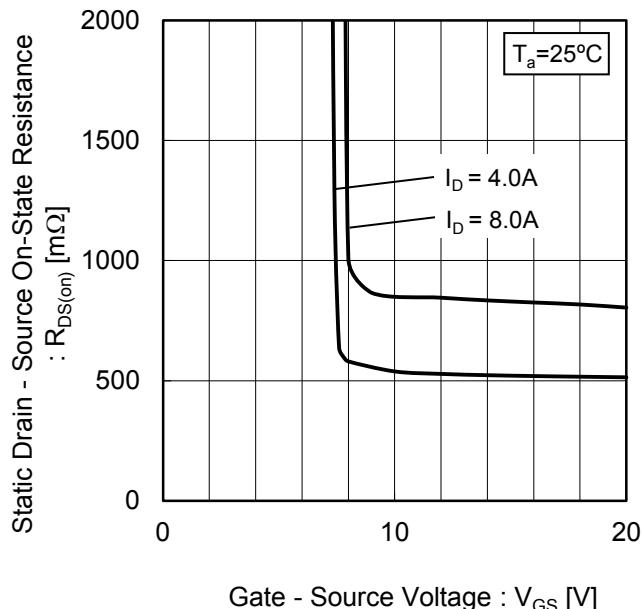


Fig.13 Static Drain - Source On - State Resistance vs. Drain Current(I_D)

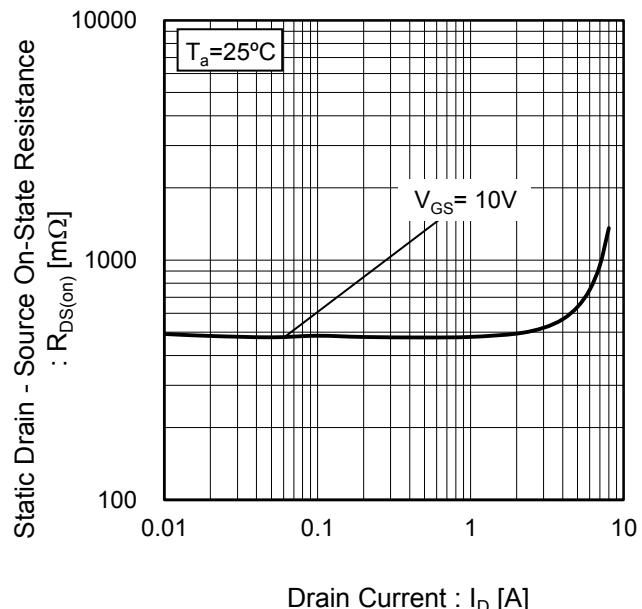
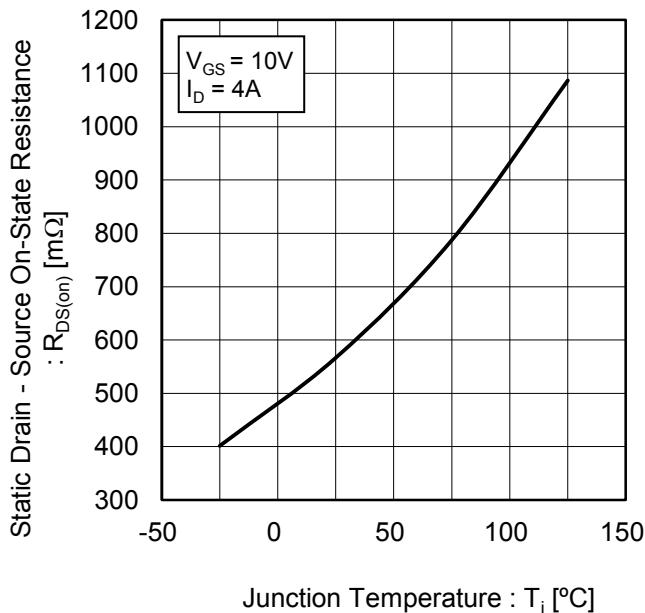
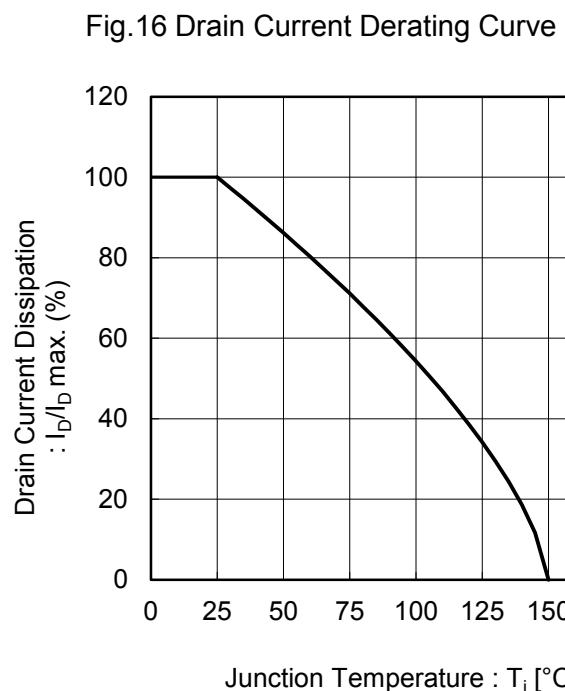
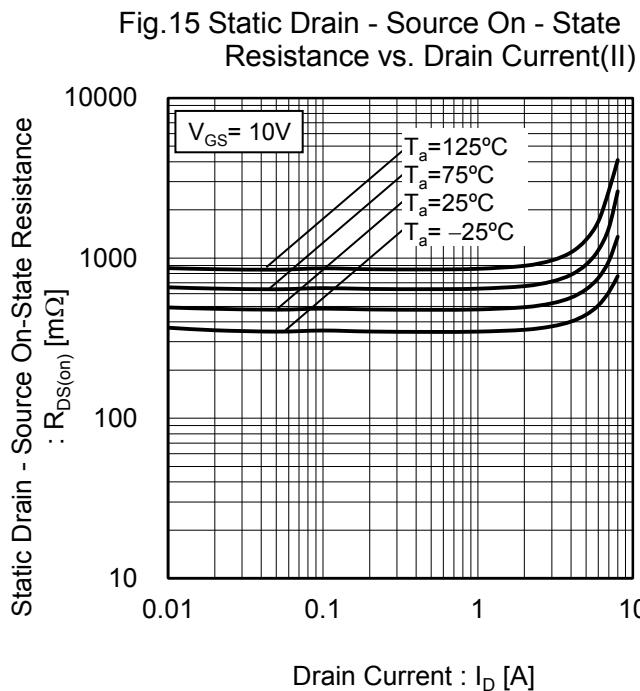


Fig.14 Static Drain - Source On - State Resistance vs. Junction Temperature



● Electrical characteristic curves



● Electrical characteristic curves

Fig.17 Typical Capacitance vs. Drain - Source Voltage

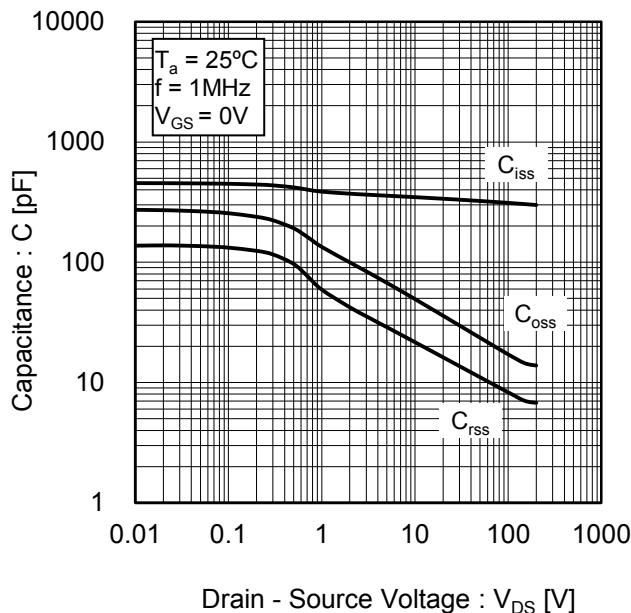


Fig.18 Switching Characteristics

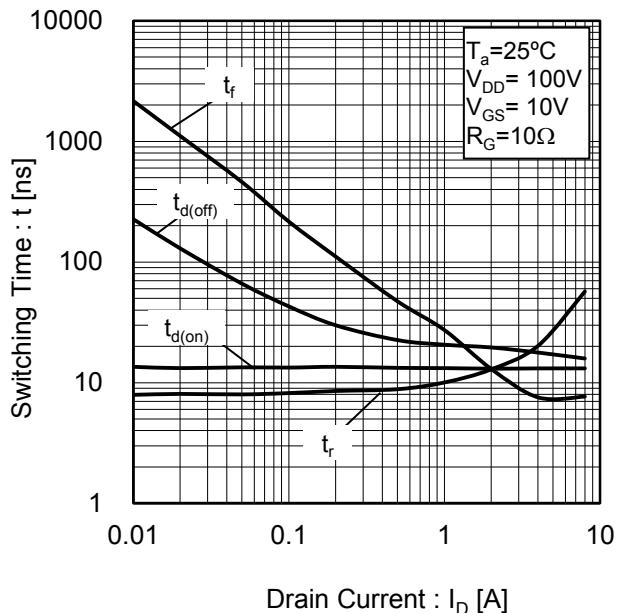
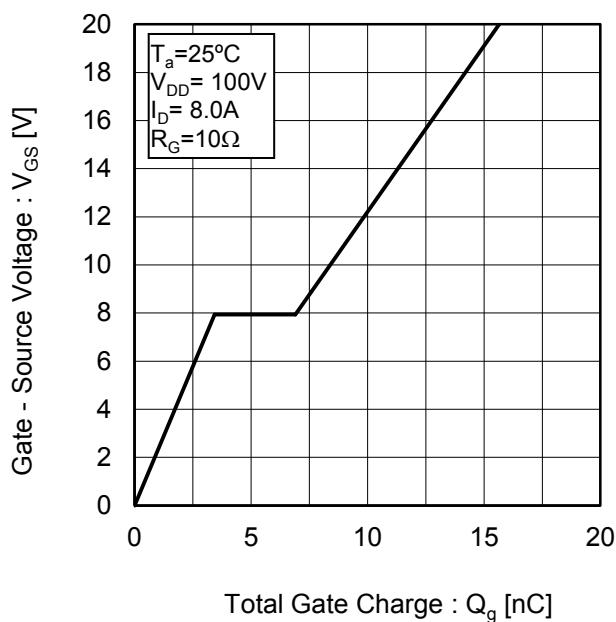


Fig.19 Dynamic Input Characteristics



●Electrical characteristic curves

Fig.20 Source Current
vs. Source - Drain Voltage

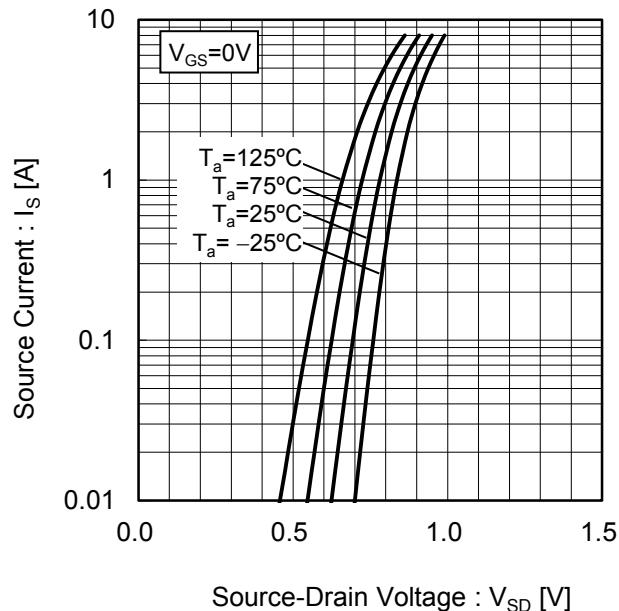
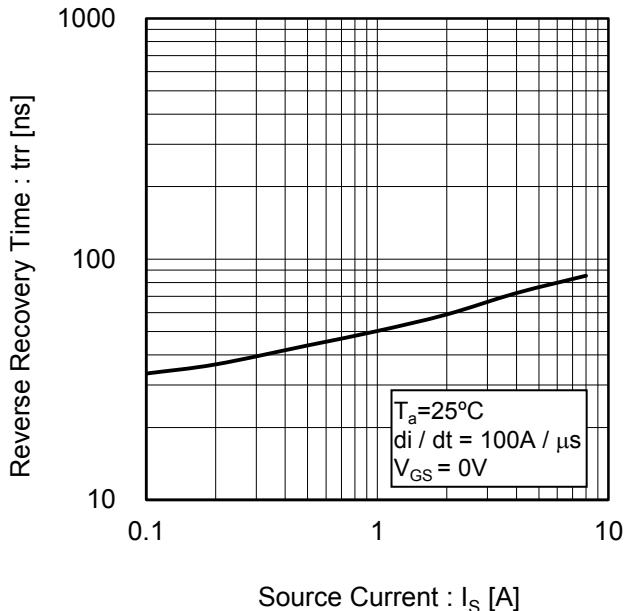


Fig21 Reverse Recovery Time
vs. Source Current



●Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

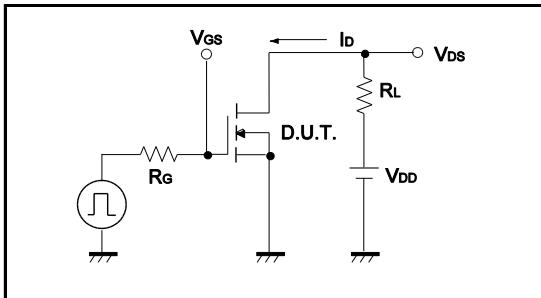


Fig.1-2 Switching Waveforms

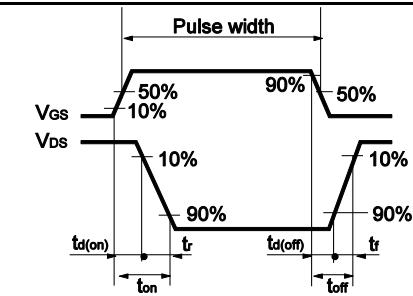


Fig.2-1 Gate Charge Measurement Circuit

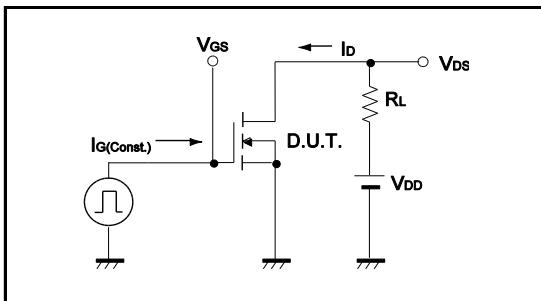


Fig.2-2 Gate Charge Waveform

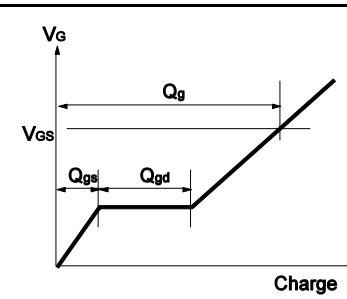


Fig.3-1 Avalanche Measurement Circuit

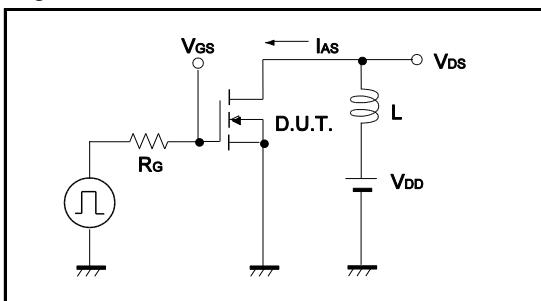
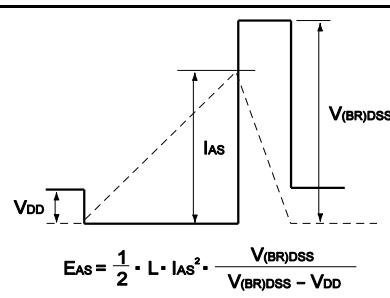
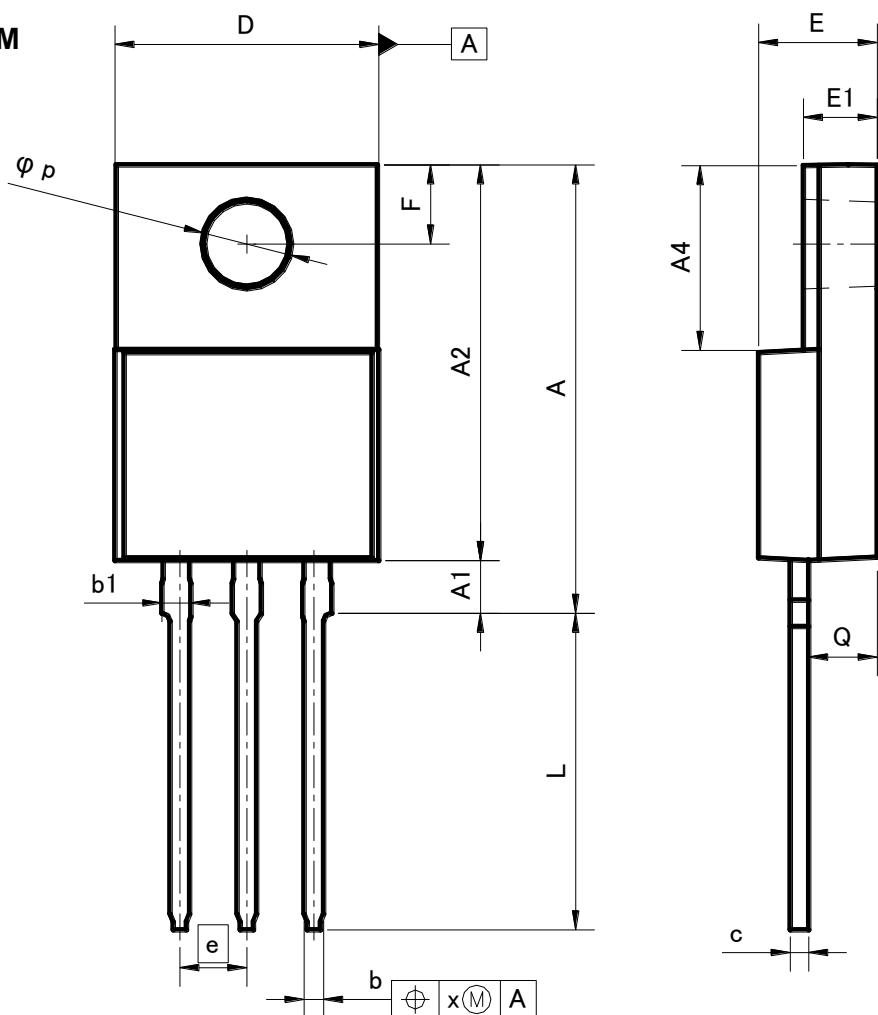


Fig.3-2 Avalanche Waveform



●Dimensions (Unit : mm)

TO-220FM



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	16.60	17.60	0.654	0.693
A1	1.80	2.20	0.071	0.087
A2	14.80	15.40	0.583	0.606
A4	6.80	7.20	0.268	0.283
b	0.70	0.85	0.028	0.033
b1	1.10	1.50	0.043	0.059
c	0.70	0.85	0.028	0.033
D	9.90	10.30	0.39	0.406
E	4.40	4.80	0.173	0.189
e	2.54		0.10	
E1	2.70	3.00	0.106	0.118
F	2.80	3.20	0.11	0.126
L	11.50	12.50	0.453	0.492
p	3.00	3.40	0.118	0.134
Q	2.10	3.10	0.083	0.122
x	-	0.381	-	0.015

Dimension in mm/inches

Notes

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